Central™
Semiconductor Corp.

PROCESS CPD96V

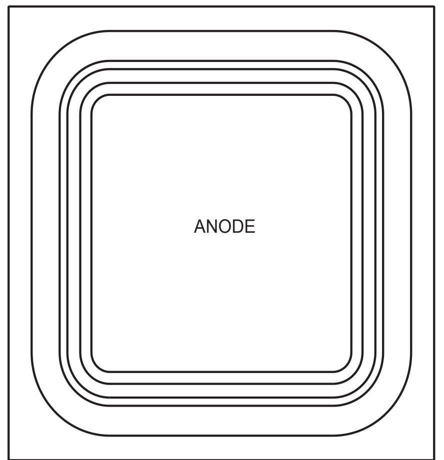
Schottky Diode

500mA Low V_F Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	16 x 16 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

28,028

PRINCIPAL DEVICE TYPES

CMHSH5-2L
CMHSH5-4

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